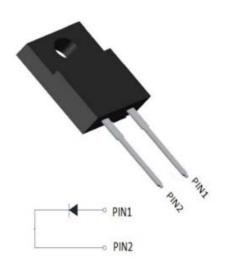






Silicon Carbide Schottky Diode

V_{RRM}	650 V
I _{F (127°C)}	6 A
Qc	25 nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery voltage
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: ITO-220AC

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106506FQG2
Reverse voltage (repetitive peak) @ T _i =25°C	V_{RRM}	٧	650
Reverse voltage (Surge Peak) @ T _j =25°C	V_{RSM}	٧	650
Reverse voltage (DC) @ T _j =25°C	V_{DC}	٧	650
Continuous forward current @ T _c =25°C		А	12
Continuous forward current @ T _c =127°C	l _F		6
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	65
Power Dissipation@ T _c =25°C		10/	31
Power Dissipation@ T _c =110°C	Ртот	W	13
i²t Value@ Tc=25°C ,tp=10ms	∫i²dt	A ² S	21
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

YJD106506FQG2

■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Company to the part disco		V	I _F =6A, T _j =25°C	1.31	1.5
Forward voltage drop	V _F		I _F =6A, T _j =175°C	1.65	-
Poverse leakage current	I _R	μА	V _R =650V, T _j =25°C	0.5	25
Reverse leakage current			V _R =650V, T _j =175°C	5	-
Total capacitive charge	Q _C	nC	V_R =400V, T_j =25°C , QC = $\int_0^{VR}C(V)dV$	25	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	378	-
			V _R =200V, f=1MHZ	51	-
			V _R =400V, f=1MHZ	49	-
Capacitance Stored Energy	Ec	μJ	V _R =400V	3	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{eJ-C}	°C W	4.76

■Typical Characteristics

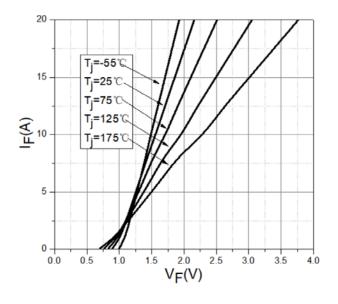


Figure 1. Forward Characteristics

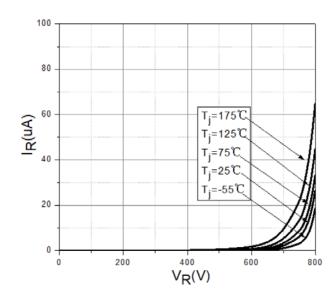
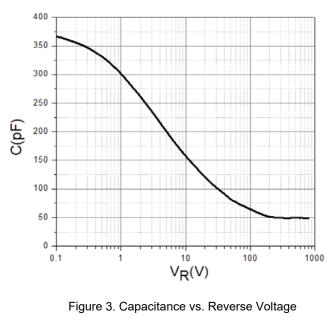
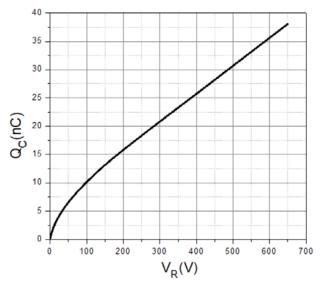
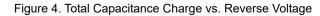
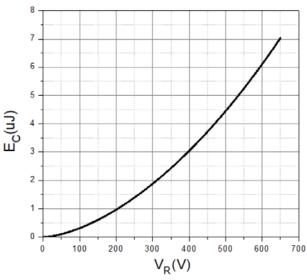


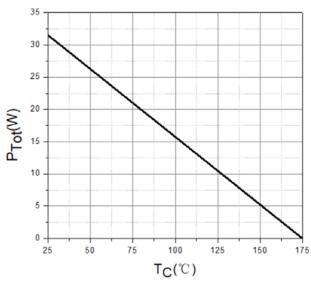
Figure2. Reverse Characteristic











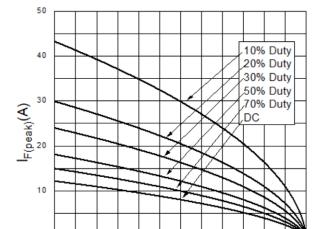
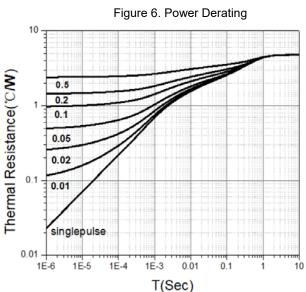


Figure 5. Capacitance Stored Energy



 $\mathsf{T}_{\mathbb{C}}({}^{\circ}\!\mathbb{C})$ Figure 7. Current Derating

100

125

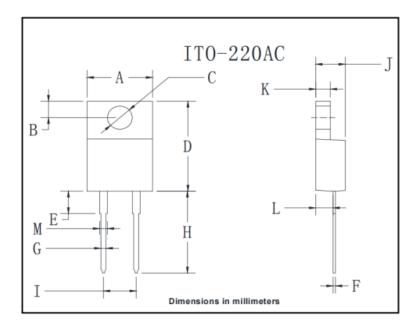
Figure 8. Transient Thermal Impedance

50

75



■Outline Dimensions



ITO-220AC				
Dim	Min	Max		
Α	9.8	10.2		
В	2.25	2.75		
С	2.95	3.45		
D	14.75	15.25		
E	3.5	4.1		
F	0.45	0.75		
G	0.45	0.75		
Н	13.35	14.15		
I	4.97	5.23		
J	4.3	4.8		
K	2.5	2.74		
L	2.58	2.82		
M	1.03	1.43		



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